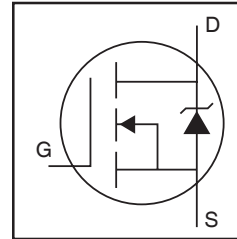


# IRFR1018EPbF IRFU1018EPbF

HEXFET® Power MOSFET

## Applications

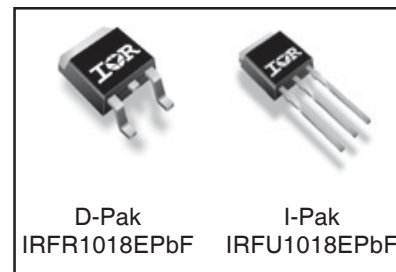
- High Efficiency Synchronous Rectification in SMPS
- Uninterruptible Power Supply
- High Speed Power Switching
- Hard Switched and High Frequency Circuits



$V_{DSS}$	<b>60V</b>
$R_{DS(on)}$ <b>typ.</b>	<b>7.1mΩ</b>
	<b>max.</b>
$I_D$ (Silicon Limited)	<b>79A</b> ①
$I_D$ (Package Limited)	<b>56A</b>

## Benefits

- Improved Gate, Avalanche and Dynamic dv/dt Ruggedness
- Fully Characterized Capacitance and Avalanche SOA
- Enhanced body diode dV/dt and dI/dt Capability



<b>G</b>	<b>D</b>	<b>S</b>
Gate	Drain	Source

## Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
$I_D$ @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V (Silicon Limited)	79①	A
$I_D$ @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V (Silicon Limited)	56①	
$I_D$ @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V (Wire Bond Limited)	56	
$I_{DM}$	Pulsed Drain Current ②	315	
$P_D$ @ $T_C = 25^\circ\text{C}$	Maximum Power Dissipation	110	W
	Linear Derating Factor	0.76	W/°C
$V_{GS}$	Gate-to-Source Voltage	± 20	V
dv/dt	Peak Diode Recovery ④	21	V/ns
$T_J$ $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	

## Avalanche Characteristics

$E_{AS}$ (Thermally limited)	Single Pulse Avalanche Energy ③	88	mJ
$I_{AR}$	Avalanche Current ②	47	A
$E_{AR}$	Repetitive Avalanche Energy ⑤	11	mJ

## Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑥	—	1.32	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount) ⑥⑦	—	50	
$R_{\theta JA}$	Junction-to-Ambient ⑥	—	110	

Notes ① through ⑦ are on page 2

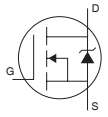
**Static @ T<sub>J</sub> = 25°C (unless otherwise specified)**

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	60	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS/ΔT<sub>J</sub></sub>	Breakdown Voltage Temp. Coefficient	—	0.073	—	V/°C	Reference to 25°C, I <sub>D</sub> = 5mA <sup>②</sup>
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	7.1	8.4	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 47A <sup>③</sup>
V <sub>GS(th)</sub>	Gate Threshold Voltage	2.0	—	4.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 100μA
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	20	μA	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 48V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -20V

**Dynamic @ T<sub>J</sub> = 25°C (unless otherwise specified)**

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
gfs	Forward Transconductance	110	—	—	S	V <sub>DS</sub> = 50V, I <sub>D</sub> = 47A
Q <sub>g</sub>	Total Gate Charge	—	46	69	nC	I <sub>D</sub> = 47A
Q <sub>gs</sub>	Gate-to-Source Charge	—	10	—		V <sub>DS</sub> = 30V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	12	—		V <sub>GS</sub> = 10V <sup>⑤</sup>
Q <sub>sync</sub>	Total Gate Charge Sync. (Q <sub>g</sub> - Q <sub>gd</sub> )	—	34	—		I <sub>D</sub> = 47A, V <sub>DS</sub> = 0V, V <sub>GS</sub> = 10V
R <sub>G(int)</sub>	Internal Gate Resistance	—	0.73	—	Ω	
t <sub>d(on)</sub>	Turn-On Delay Time	—	13	—	ns	V <sub>DD</sub> = 39V
t <sub>r</sub>	Rise Time	—	35	—		I <sub>D</sub> = 47A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	55	—		R <sub>G</sub> = 10Ω
t <sub>f</sub>	Fall Time	—	46	—		V <sub>GS</sub> = 10V <sup>⑤</sup>
C <sub>iss</sub>	Input Capacitance	—	2290	—		V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	270	—		V <sub>DS</sub> = 50V
C <sub>rfs</sub>	Reverse Transfer Capacitance	—	130	—	pF	f = 1.0MHz
C <sub>oss eff. (ER)</sub>	Effective Output Capacitance (Energy Related) <sup>④</sup>	—	390	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V to 60V <sup>⑦</sup>
C <sub>oss eff. (TR)</sub>	Effective Output Capacitance (Time Related) <sup>⑤</sup>	—	630	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V to 60V <sup>⑥</sup>

**Diode Characteristics**

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	79 <sup>①</sup>	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) <sup>②</sup>	—	—	315		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 47A, V <sub>GS</sub> = 0V <sup>⑤</sup>
t <sub>rr</sub>	Reverse Recovery Time	—	26	39	ns	T <sub>J</sub> = 25°C V <sub>R</sub> = 51V, T <sub>J</sub> = 125°C I <sub>F</sub> = 47A
Q <sub>rr</sub>	Reverse Recovery Charge	—	24	36	nC	T <sub>J</sub> = 25°C T <sub>J</sub> = 125°C
I <sub>RRM</sub>	Reverse Recovery Current	—	1.8	—	A	T <sub>J</sub> = 25°C
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

**Notes:**

- ① Calculated continuous current based on maximum allowable junction temperature. Bond wire current limit is 56A. Note that current limitations arising from heating of the device leads may occur with some lead mounting arrangements.
- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ Limited by T<sub>Jmax</sub>, starting T<sub>J</sub> = 25°C, L = 0.08mH  
R<sub>G</sub> = 25Ω, I<sub>AS</sub> = 47A, V<sub>GS</sub> = 10V. Part not recommended for use above this value.
- ④ I<sub>SD</sub> ≤ 47A, di/dt ≤ 1668A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>J</sub> ≤ 175°C.
- ⑤ Pulse width ≤ 400μs; duty cycle ≤ 2%.
- ⑥ C<sub>oss eff. (TR)</sub> is a fixed capacitance that gives the same charging time as C<sub>oss</sub> while V<sub>DS</sub> is rising from 0 to 80% V<sub>DSS</sub>.
- ⑦ C<sub>oss eff. (ER)</sub> is a fixed capacitance that gives the same energy as C<sub>oss</sub> while V<sub>DS</sub> is rising from 0 to 80% V<sub>DSS</sub>.
- ⑧ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.
- ⑨ R<sub>θ</sub> is measured at T<sub>J</sub> approximately 90°C.



Fig 1. Typical Output Characteristics

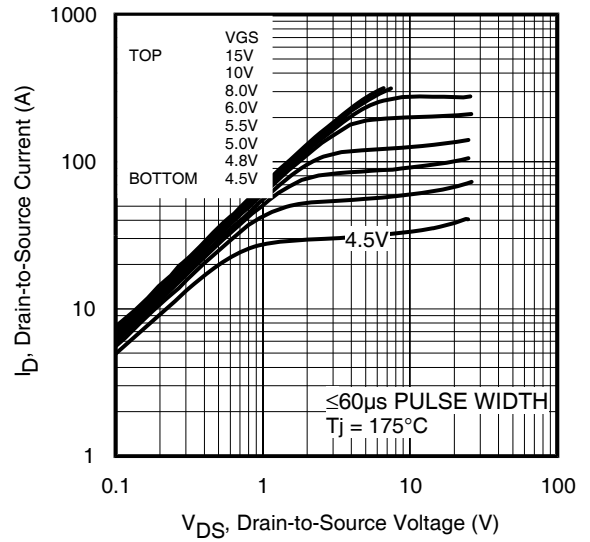


Fig 2. Typical Output Characteristics

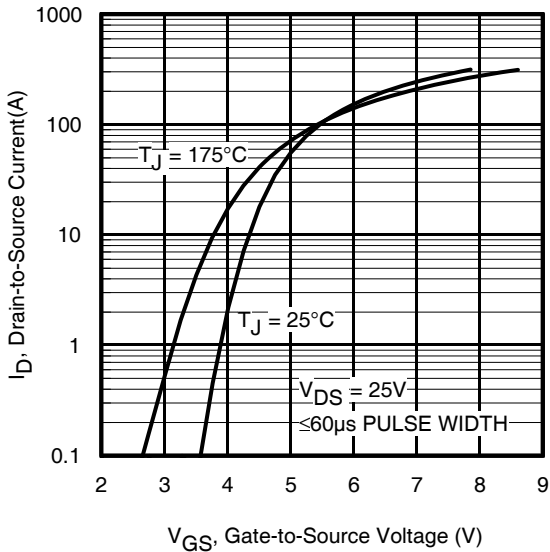


Fig 3. Typical Transfer Characteristics

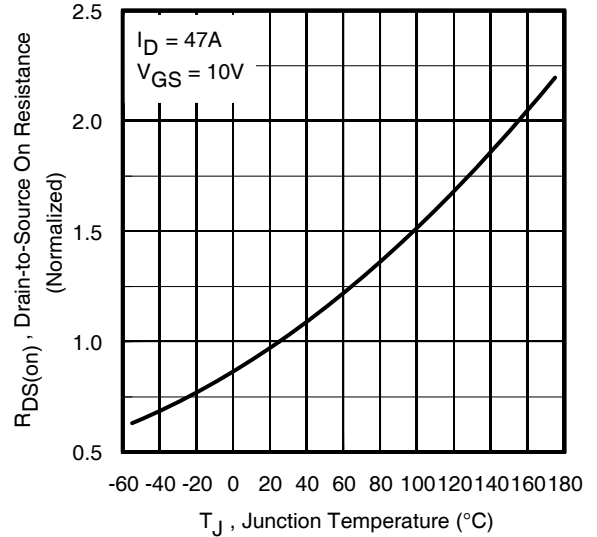


Fig 4. Normalized On-Resistance vs. Temperature



Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

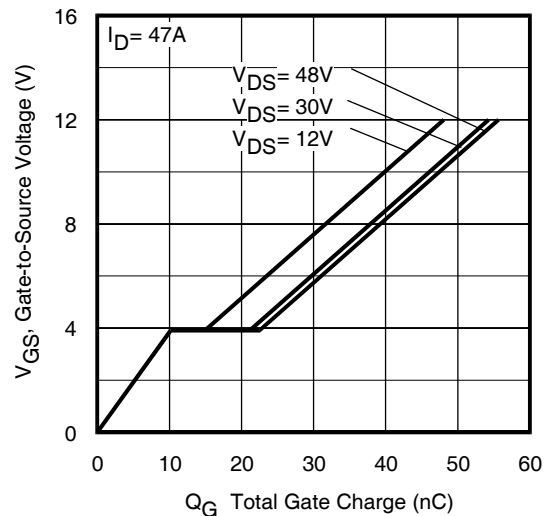


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

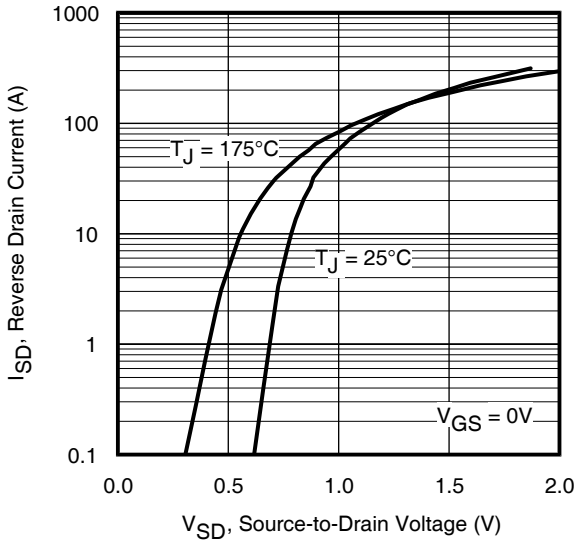


Fig 7. Typical Source-Drain Diode Forward Voltage

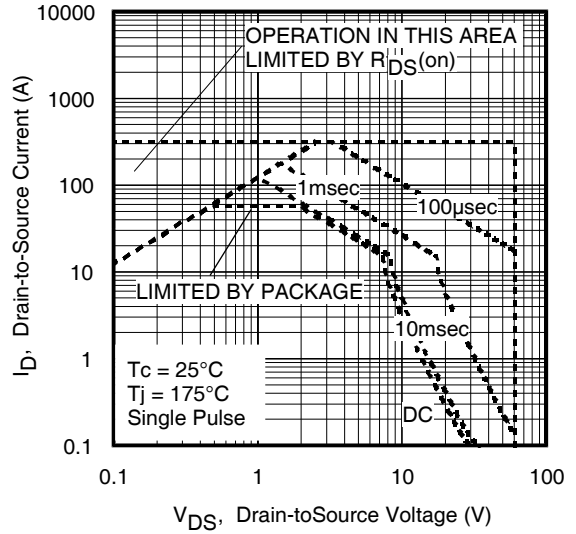


Fig 8. Maximum Safe Operating Area

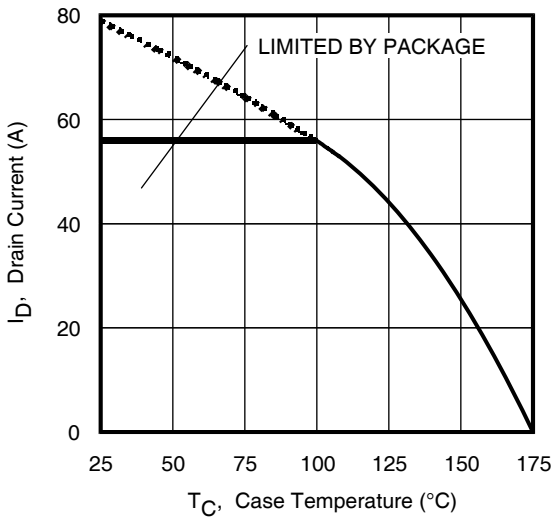


Fig 9. Maximum Drain Current vs. Case Temperature

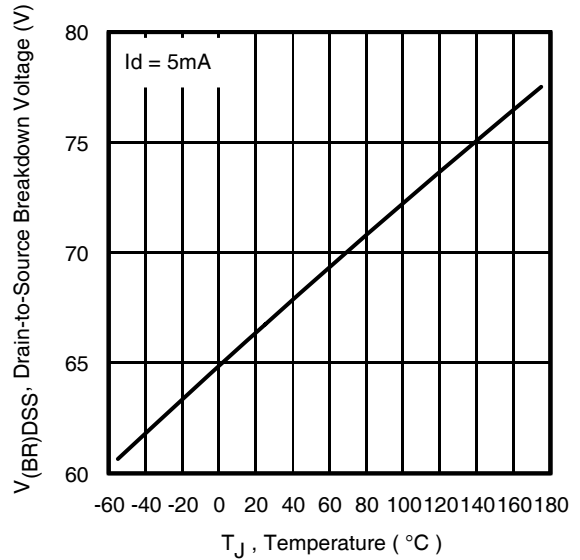


Fig 10. Drain-to-Source Breakdown Voltage

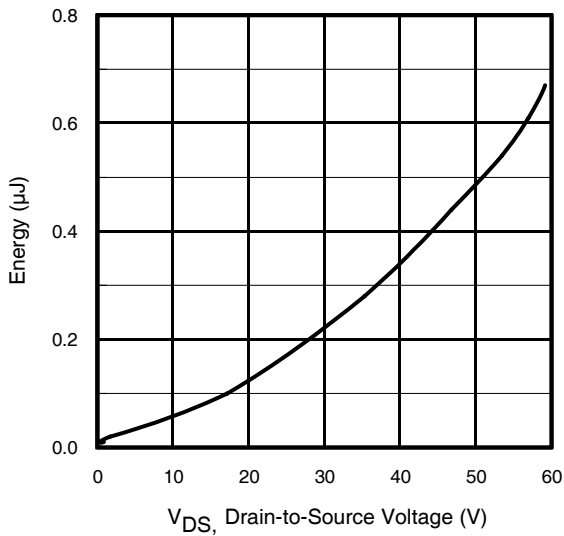


Fig 11. Typical  $C_{OSS}$  Stored Energy

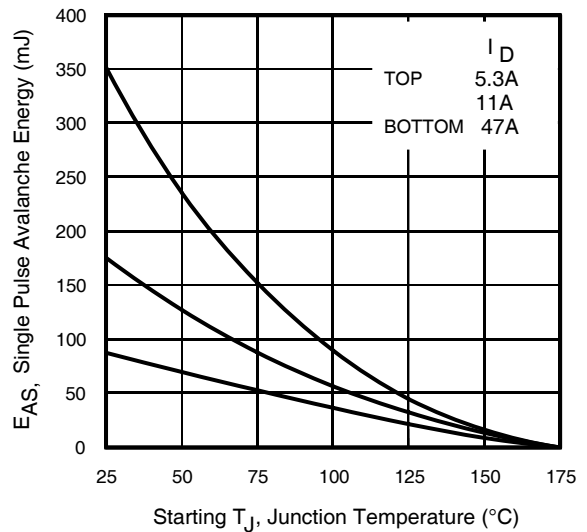


Fig 12. Maximum Avalanche Energy vs. Drain Current  
www.irf.com

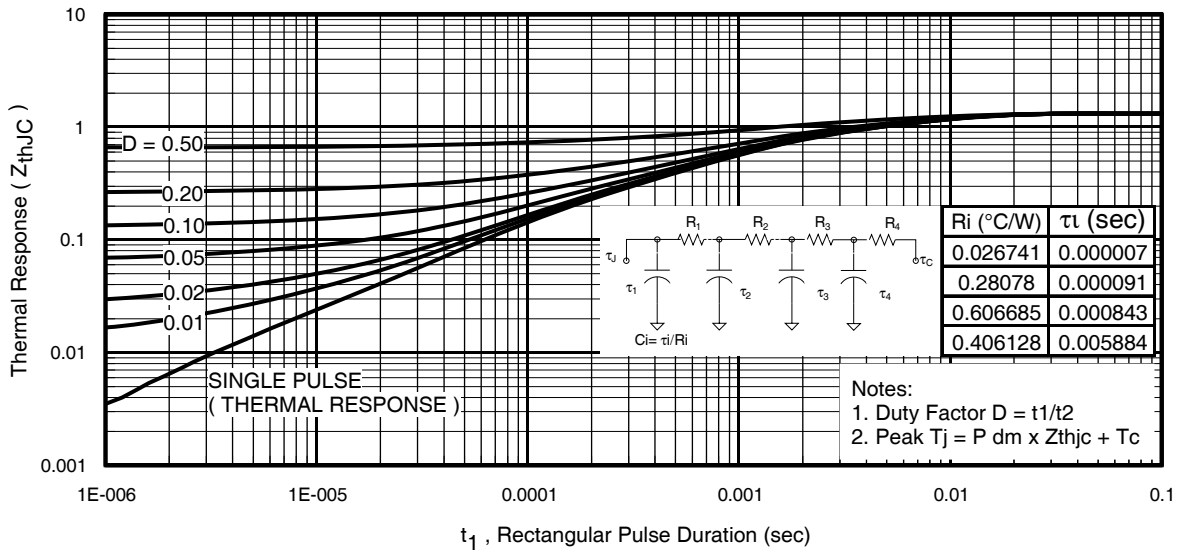


Fig 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case

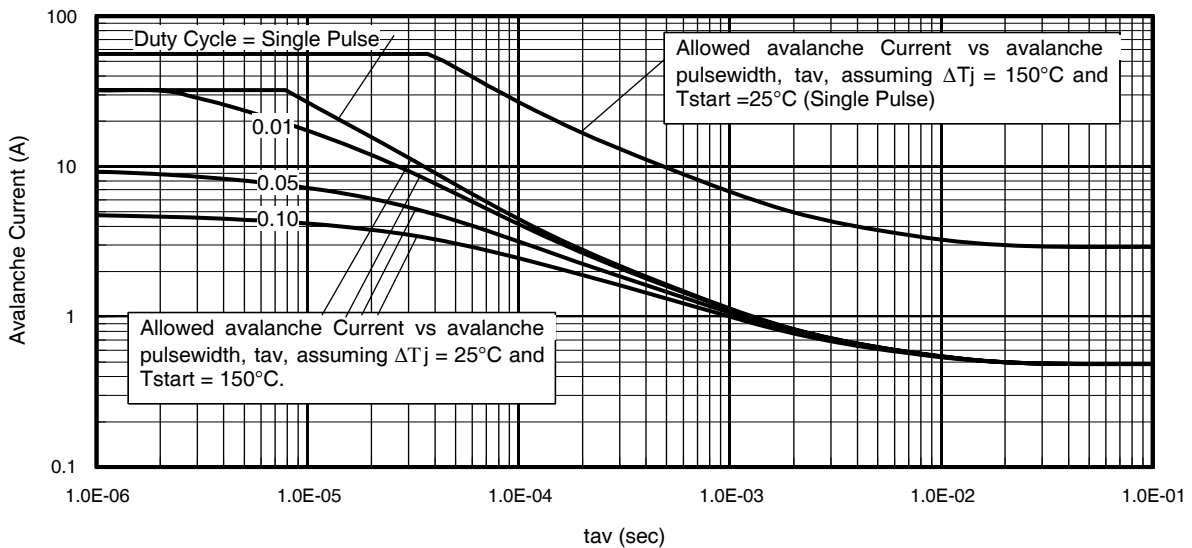
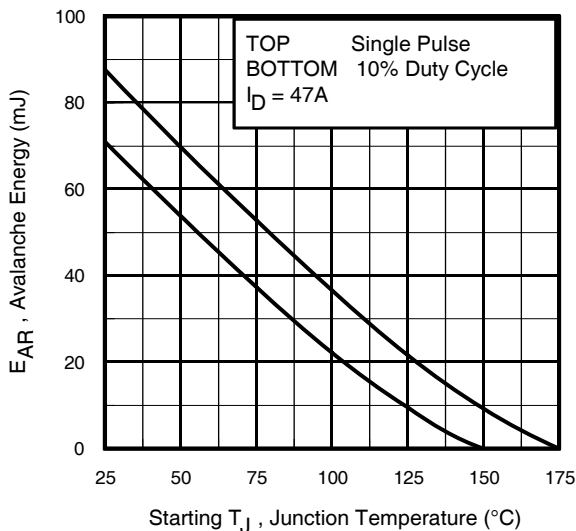


Fig 14. Typical Avalanche Current vs. Pulsewidth



Notes on Repetitive Avalanche Curves, Figures 14, 15:  
(For further info, see AN-1005 at [www.irf.com](http://www.irf.com))

1. Avalanche failures assumption:  
Purely a thermal phenomenon and failure occurs at a temperature far in excess of  $T_{jmax}$ . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as  $T_{jmax}$  is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 16a, 16b.
4.  $P_{D(ave)}$  = Average power dissipation per single avalanche pulse.
5.  $BV$  = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6.  $I_{av}$  = Allowable avalanche current.
7.  $\Delta T$  = Allowable rise in junction temperature, not to exceed  $T_{jmax}$  (assumed as 25°C in Figure 14, 15).  
 $t_{av}$  = Average time in avalanche.  
 $D$  = Duty cycle in avalanche =  $t_{av} \cdot f$   
 $Z_{thJC}(D, t_{av})$  = Transient thermal resistance, see Figures 13)

$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

Fig 15. Maximum Avalanche Energy vs. Temperature

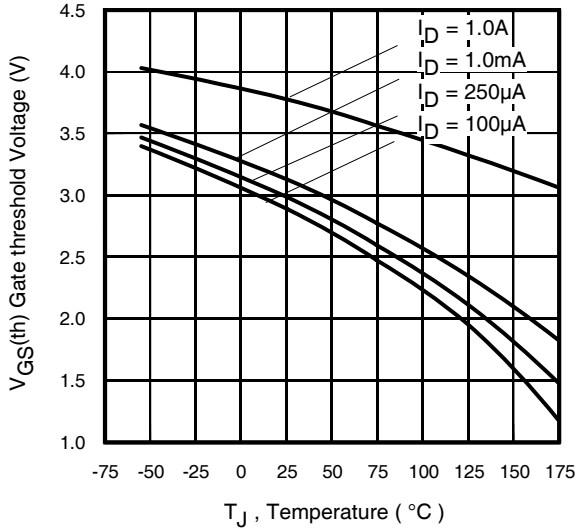


Fig 16. Threshold Voltage vs. Temperature

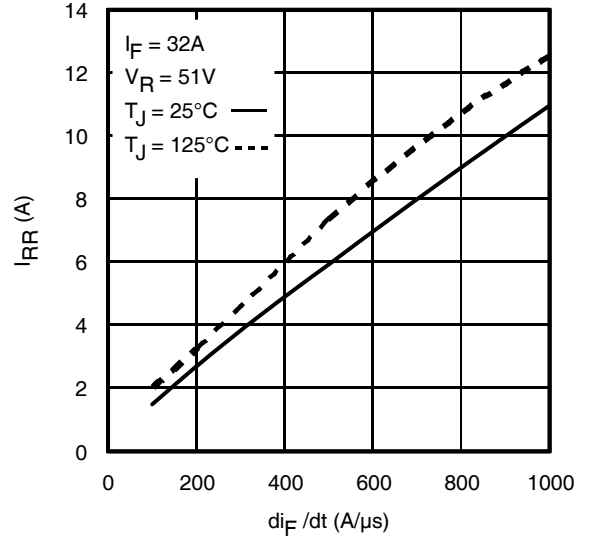


Fig. 17 - Typical Recovery Current vs.  $di_F/dt$

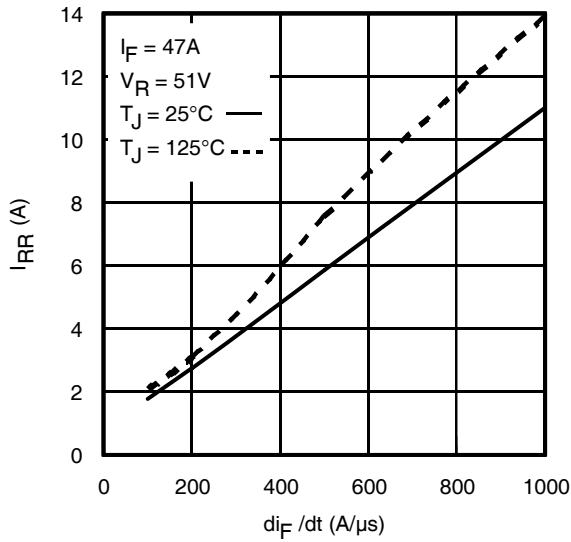


Fig. 18 - Typical Recovery Current vs.  $di_F/dt$

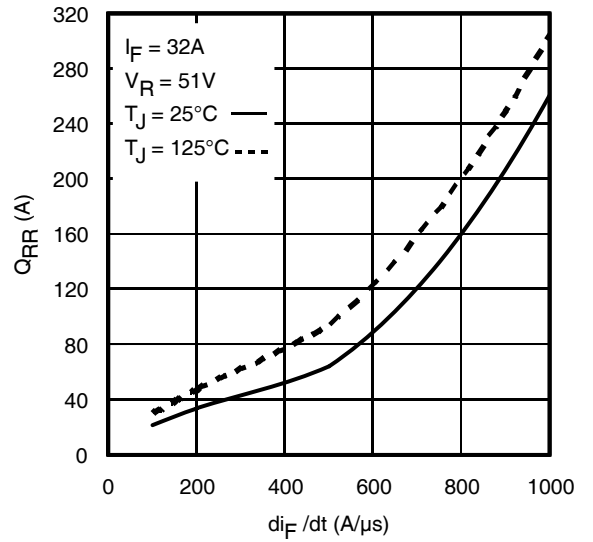


Fig. 19 - Typical Stored Charge vs.  $di_F/dt$

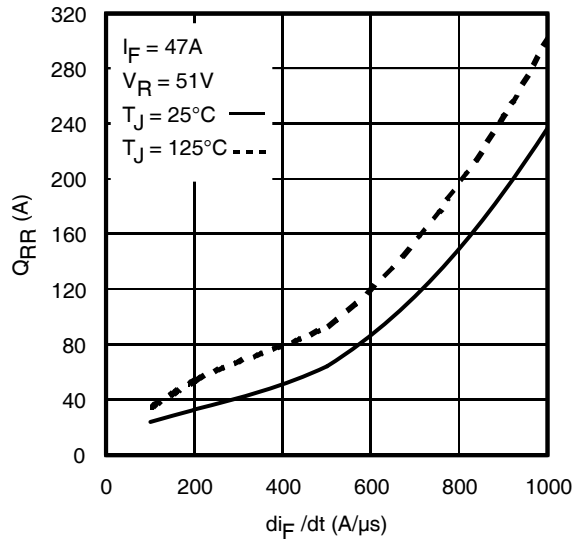
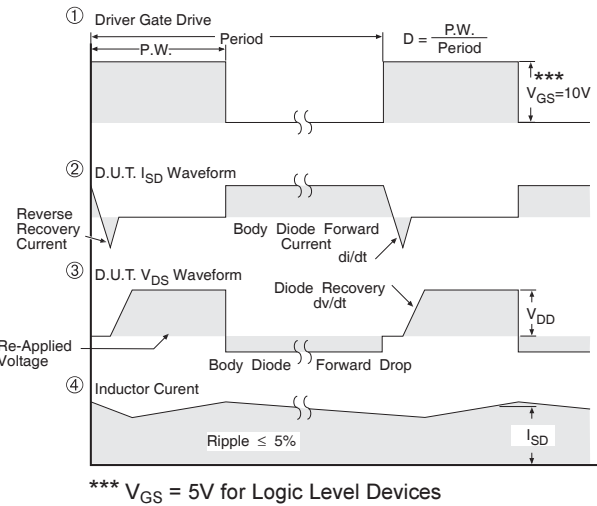
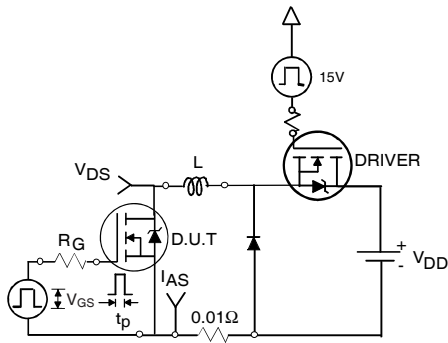


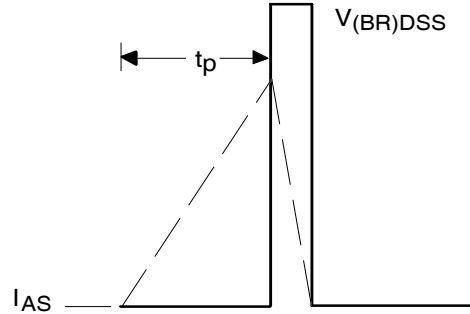
Fig. 20 - Typical Stored Charge vs.  $di_F/dt$



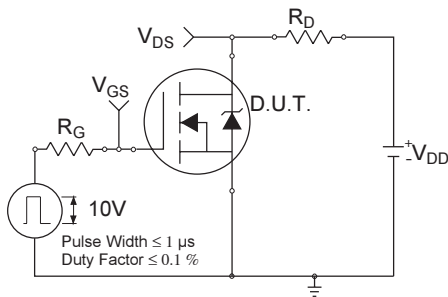
**Fig 21.** Diode Reverse Recovery Test Circuit for HEXFET® Power MOSFETs



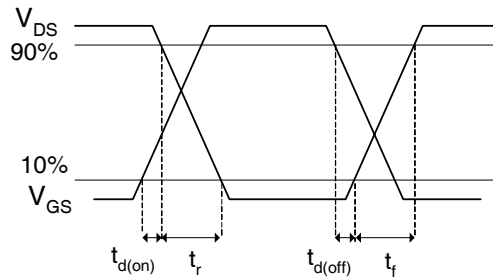
**Fig 22a.** Unclamped Inductive Test Circuit



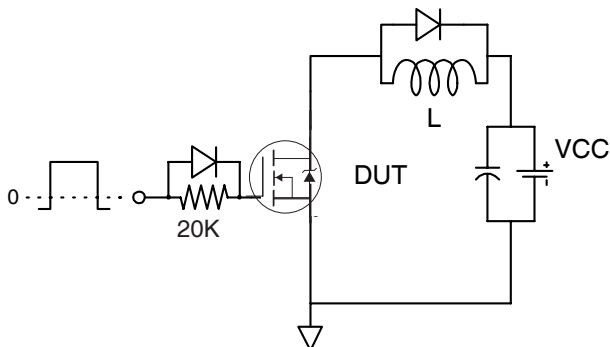
**Fig 22b.** Unclamped Inductive Waveforms



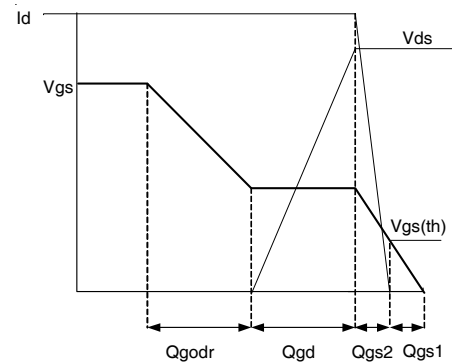
**Fig 23a.** Switching Time Test Circuit



**Fig 23b.** Switching Time Waveforms



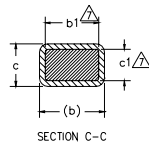
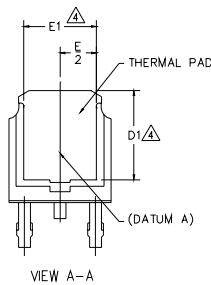
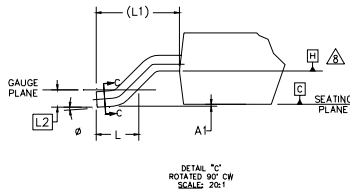
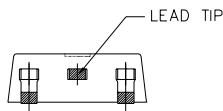
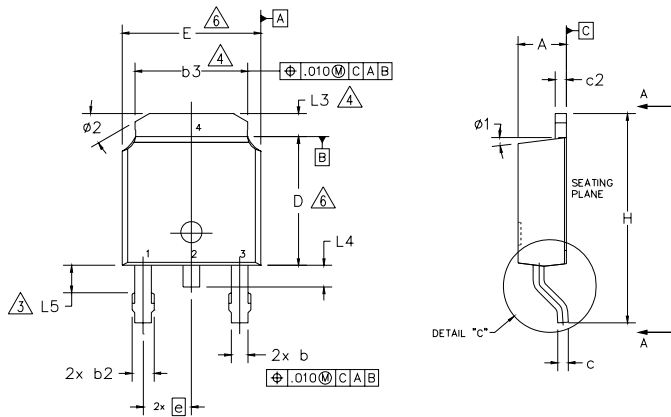
**Fig 24a.** Gate Charge Test Circuit



**Fig 24b.** Gate Charge Waveform

D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
- 2.- DIMENSION ARE SHOWN IN INCHES [MILLIMETERS].
- 3.- LEAD DIMENSION UNCONTROLLED IN L5.
- 4.- DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
- 5.- SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.10 [0.13 AND 0.25] FROM THE LEAD TIP.
- 6.- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
- 7.- DIMENSION b1 & c1 APPLIED TO BASE METAL ONLY.
- 8.- DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
- 9.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	7
A1	-	0.13	-	.005	
b	0.64	0.89	.025	.035	
b1	0.65	0.79	.025	.031	
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	
c2	0.46	0.89	.018	.035	
D	5.97	6.22	.235	.245	
D1	5.21	-	.205	-	4
E	6.35	6.73	.250	.265	6
E1	4.32	-	.170	-	4
e	2.29 BSC		.090 BSC		LEAD ASSIGNMENTS
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74 BSC		.108 REF.		
L2	0.51 BSC		.020 BSC		HEXFET
L3	0.89	1.27	.035	.050	
L4	-	1.02	-	.040	
L5	1.14	1.52	.045	.060	
ø	0"	10"	0"	10"	
ø1	0"	15"	0"	15"	IGBT & CoPAK
ø2	25"	35"	25"	35"	

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBT & CoPAK

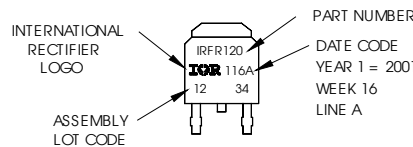
- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

D-Pak (TO-252AA) Part Marking Information

EXAMPLE: THIS IS AN IRFR120 WITH ASSEMBLY LOT CODE 1234 ASSEMBLED ON WW 16, 2001 IN THE ASSEMBLY LINE "A"

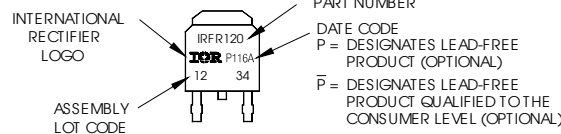
Note: "P" in assembly line position indicates "Lead-Free"

"P̄" in assembly line position indicates "Lead-Free" qualification to the consumer-level



PART NUMBER  
DATE CODE  
YEAR 1 = 2001  
WEEK 16  
LINE A

OR



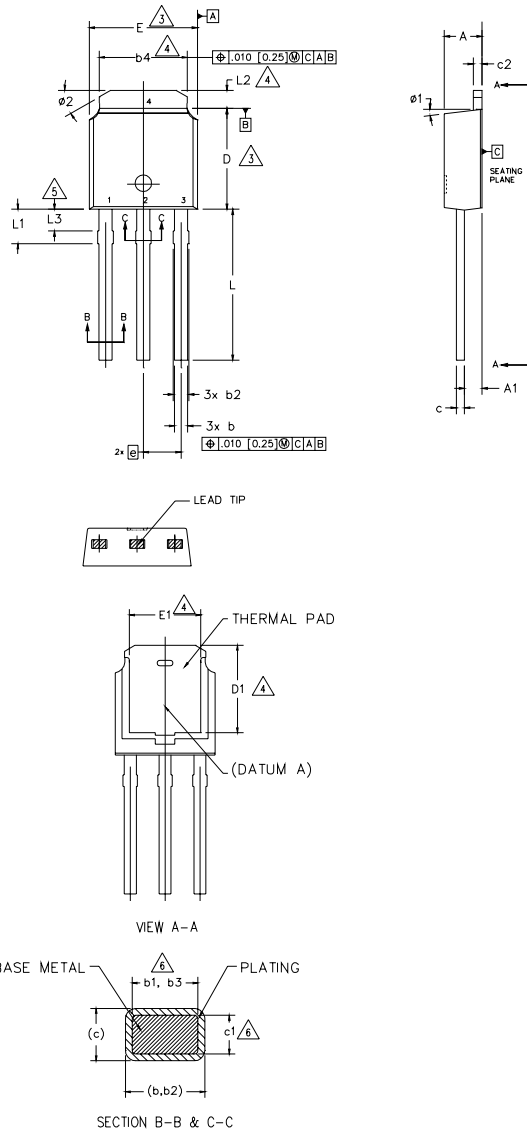
PART NUMBER  
DATE CODE  
P = DESIGNATES LEAD-FREE PRODUCT (OPTIONAL)  
P̄ = DESIGNATES LEAD-FREE PRODUCT QUALIFIED TO THE CONSUMER LEVEL (OPTIONAL)  
YEAR 1 = 2001  
WEEK 16  
A = ASSEMBLY SITE CODE

Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>



# I-Pak (TO-251AA) Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
- 2.- DIMENSION ARE SHOWN IN INCHES [MILLIMETERS].
- 3.- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
- 4.- THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
- 5.- LEAD DIMENSION UNCONTROLLED IN L3.
- 6.- DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
- 7.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA (Date 06/02).
- 8.- CONTROLLING DIMENSION : INCHES.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1	0.89	1.14	.035	.045	
b	0.64	0.89	.025	.035	6
b1	0.65	0.79	.025	.031	
b2	0.76	1.14	.030	.045	6
b3	0.76	1.04	.030	.041	
b4	4.95	5.46	.195	.215	4
c	0.46	0.61	.018	.024	6
c1	0.41	0.56	.016	.022	
c2	0.46	0.89	.018	.035	3
D	5.97	6.22	.235	.245	
D1	5.21	-	.205	-	4
E	6.35	6.73	.250	.265	3
E1	4.32	-	.170	-	4
e	2.29 BSC		.090 BSC		
L	8.89	9.65	.350	.380	4
L1	1.91	2.29	.045	.090	
L2	0.89	1.27	.035	.050	5
L3	1.14	1.52	.045	.060	
phi1	0"	15"	0"	15"	
phi2	25"	35"	25"	35"	

LEAD ASSIGNMENTS

HEXFET

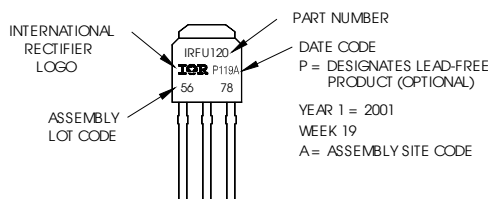
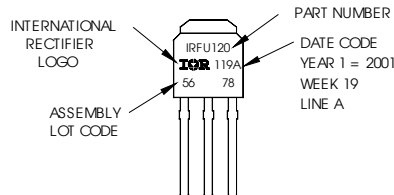
- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

# I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120 WITH ASSEMBLY LOT CODE 5678 ASSEMBLED ON WW 19, 2001 IN THE ASSEMBLY LINE "A"

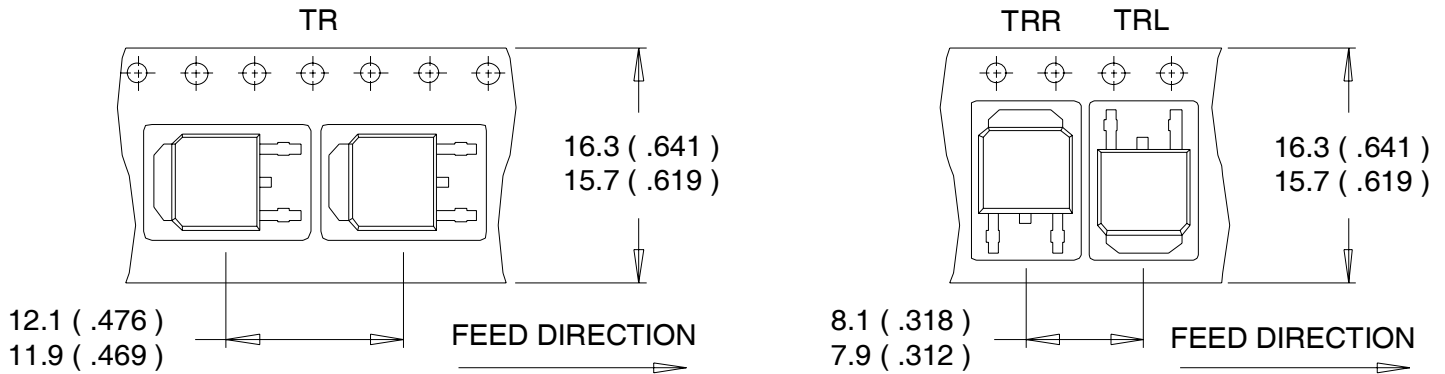
Note: "P" in assembly line position indicates Lead-Free'

OR



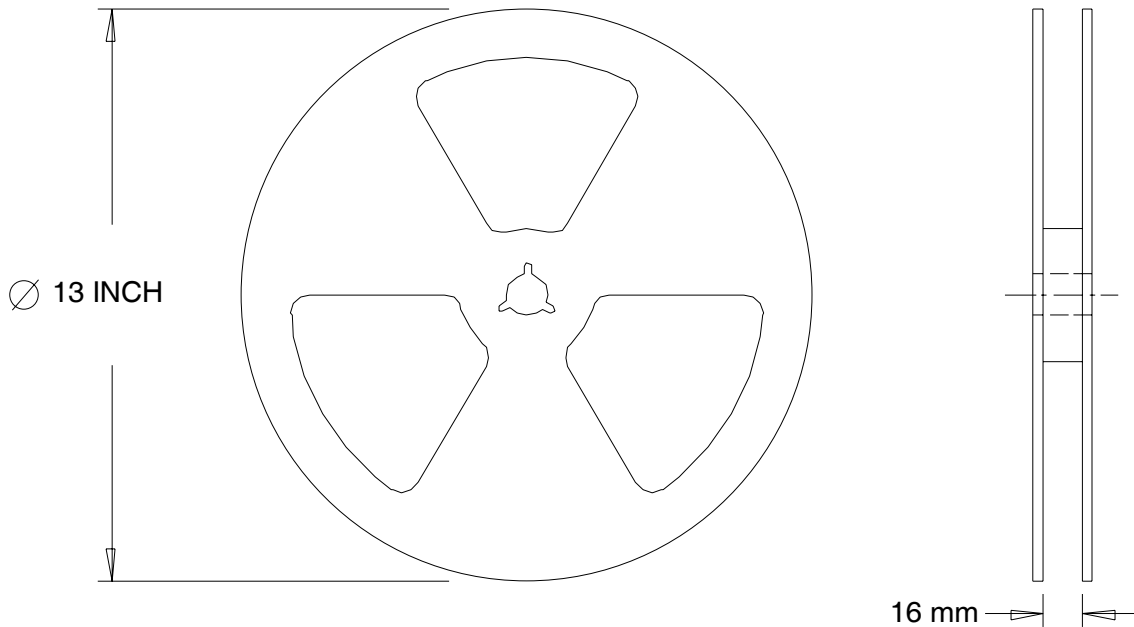
Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

**D-Pak (TO-252AA) Tape & Reel Information**  
Dimensions are shown in millimeters (inches)



**NOTES :**

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS ( INCHES ).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



**NOTES :**

1. OUTLINE CONFORMS TO EIA-481.

Data and specifications subject to change without notice.  
This product has been designed for the industrial market.  
Qualification Standards can be found on IR's Web site.